

09-13-2000



MRD
8/15/00

ASSIGNM.

101454802 SHEET
-PATENTS ONLY-

To: Honorable Commissioner of Patents and Trademarks:

Please record the attached original document(s) or copy thereof.

1. Name of conveying party(ies)
a) United Semiconductor Corp.

2. Name and address of receiving party(ies):
a) Name: United Microelectronics Corp.
Address: No. 3, Li-Hsin Rd. 2
Science-Based Industrial Park
Hsinchu, Taiwan
R.O.C.

3. Nature of conveyance
- | | | | |
|-------------------------------------|--------------------|--------------------------|-------------------|
| <input checked="" type="checkbox"/> | Assignment | <input type="checkbox"/> | Merger |
| <input type="checkbox"/> | Security Agreement | <input type="checkbox"/> | Change of Name |
| <input type="checkbox"/> | Other _____ | <input type="checkbox"/> | License Agreement |

Execution Date: July 19, 2000

4. Application Number(s) or Patent Number(s): See Appendix A

The title of the (new) application is:

See Appendix A

5. Please send all correspondence concerning this (these) documents to:

HICKMAN COLEMAN & HUGHES, LLP
P.O. Box 52037
Palo Alto, CA 94303-0746
Tel. No.: (650) 470-7430
Fax No.: (650) 470-7440

6. Total number of applications and patents involved: 11

7. Total fee (37 CFR 3.41): \$440.00

- ☒ Enclosed
☐ Authorized to be charged to Deposit Account No. 50-0384
(Order No. JCIPG000)

8. To the best of my knowledge and belief, the foregoing information is true and correct and any attached copy is a true copy of the original document.

Date: August 9, 2000

Paul L. Hickman
Registration No. 28,516

09/12/2000 MTHA11 00000448 09466685

01 FC:581

440.00 DP

Attorney Docket No. JCIPG000

(Revised 01/96)

PATENT
REEL: 011050 FRAME: 0484

Appendix A

Title	Filing/Issue Date	Serial/Patent No.
METHOD OF MANUFACTURING DYNAMIC RANDOM ACCESS MEMORY	1999/12/20	09/466,685
FLASH MEMORY STRUCTURE AND METHOD OF MANUFACTURE	1999/12/20	09/467,251
METHOD OF FORMING AN INTERMETAL DIELECTRIC LAYER	1999/12/22	09/471,055
METHOD FOR IMPROVING YIELD OF CIRCUIT REPAIR	1999/12/22	09/470,247
METHOD OF FABRICATING CAPACITOR	1999/12/20	09/467,590
STRUCTURE FOR ESD PROTECTION WITH SINGLE CRYSTAL SILICON SIDED JUNCTION DIODE	1999/12/21	09/467,675
FABRICATION METHOD FOR AN INTERCONNECT STRUCTURE	1999/12/20	09/467,459
METHOD FOR FABRICATING AN INTERCONNECT	1999/12/20	09/466,686
METHOD OF STABILIZING ANTI-REFLECTION COATING LAYER	1999/12/20	09/467,260
METHOD OF STABILIZING ANTI-REFLECTION COATING LAYER	1999/12/20	09/467,284
METHOD OF IMPROVING QUALITY OF POLYSILICON/GATE OXIDE INTERFACE	1999/12/20	09/467,286

ASSIGNMENT OF PATENTS AND PATENT APPLICATIONS

United Semiconductor Corp., A Taiwanese corporation having a place of business at No. 3, Li-Hsin Rd. 2, Science-Based Industrial Park, Hsinchu, Taiwan, R.O.C., (hereafter ASSIGNOR) has been assigned or otherwise has an ownership interest in certain new and useful improvements as set forth in the patents and patent applications listed in attached Appendix A.

For good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged, ASSIGNOR hereby:

- 1) Sell(s), assign(s) and transfer(s) to United Microelectronics Corp., a Taiwanese corporation having a place of business at No. 3, Li-Hsin Rd. 2, Science-Based Industrial Park, Hsinchu, Taiwan, R.O.C. (hereinafter referred to as "ASSIGNEE") the entire right, title and interest in any and all improvements and inventions disclosed in, application(s) based upon, and Patent(s) (including foreign patents) granted upon the information which is disclosed therein.
- 2) Authorize and request the Commissioner of Patents to issue any and all Letters Patents resulting from said application(s) or any division(s), continuation(s), substitute(s), re-examination(s) or reissue(s) thereof to the ASSIGNEE.
- 3) Agree to execute all papers and documents and, entirely at the ASSIGNEE's expense, perform any acts which are reasonably necessary in connection with the prosecution of said application(s), as well as any derivative and applications thereof, foreign applications based thereon, and/or the enforcement of patents resulting from such applications.
- 4) Agree that the terms, covenants and conditions of this assignment shall inure to the benefit of the ASSIGNEE, its successors, assigns and other legal representative(s), and shall be binding upon the inventor(s), as well as the inventor's heirs, legal representatives and assigns.
- 5) Warrant and represent that ASSIGNOR has not entered, and will not enter into any assignment, contract, or understanding that conflicts with this assignment.

Signed on the date(s) indicated beside my (our) signature(s).

United Semiconductor Corp.

By: _____

Typed Name: Peter Chang

President

United Semiconductor Corp.

Date: 7.19/00

Witnesses:

Signature _____

Wilson H.L. Lee

7F-1, No. 100, Roosevelt Rd., Sec. 2

Taipei, Taiwan, R.O.C.

Date: July 19, 2000

Signature _____

Felix Yeh

7F-1, No. 100, Roosevelt Rd., Sec. 2

Taipei, Taiwan, R.O.C.

Date: July 19, 2000

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